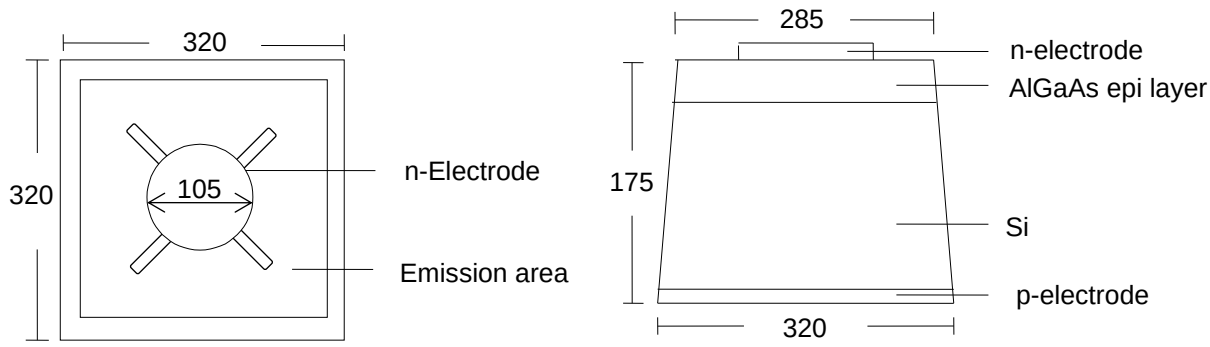
## Features :

- Suitable for New Creative Products

## Typical Applications :

- Home entertainment
- Light source for CMOS & CCD camera
- Security camera, CCTV

## Outline Dimensions : (Unit: um)




## Physical Structure :

| | | |
|---|---|---|
| LED Chip dimension | Chip size | 320 x 320± 25 um |
| | Thickness | 175 ± 25 um |
| | Emission area | 285 um |
| | Bonding pad | 105 um |
| Electrode | Top: N (cathode) | Gold |
| | Backside: P (anode) | Gold |
| Surface condition | Frosted | |

*D2

## Electro-Optical Characteristics : (Ta = 25℃)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| Forward voltage | $V_{FH}$ | $I_F$ = 100 mA | 1.30 | - | 1.60 | V |
| Reverse current | $I_R$ | $V_R$ = 10V | - | - | 1 | μA |
| Radiant Power | $P_o$ | $I_F$ = 100 mA | 16 | - | 26 | mW |
| Wavelength | $\lambda_P$ | $I_F$ = 100 mA | 940 | 945 | 950 | nm |
| Spectral width at half height | △λ | $I_F$ = 100 mA | - | 45 | - | nm |

## Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

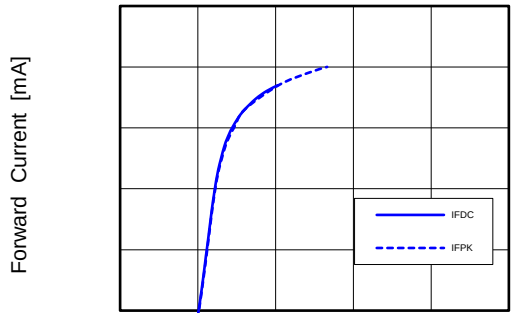



Fig 2. Relative Radiant Power vs. Wavelength

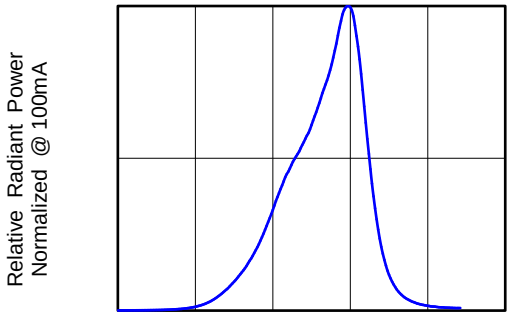



Fig 3. Relative Radiant Power vs. Forward DC Current

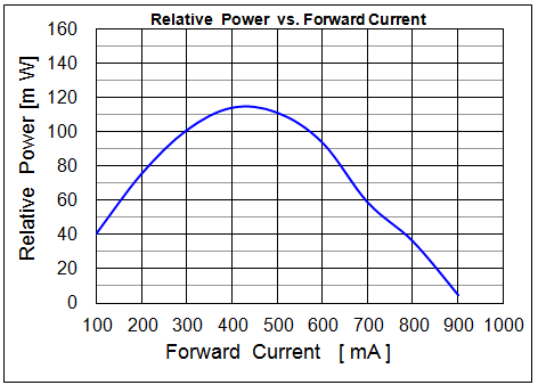



Fig 4. Relative Radiant Power vs. Forward Peak Current

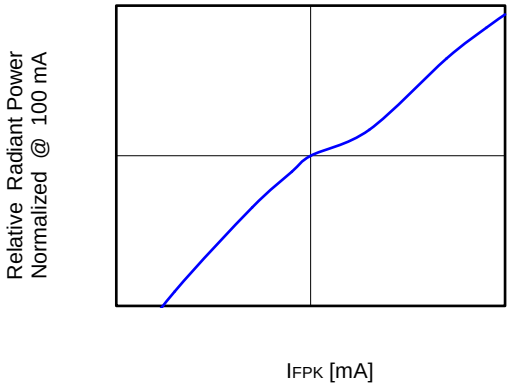



Fig 5. Forward DC Voltage vs. Temperature

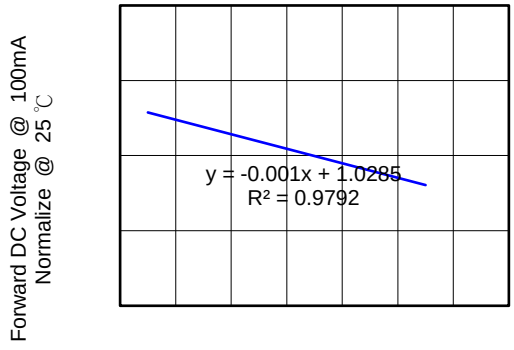



Fig 6. Relative Radiant Power vs. Temperature

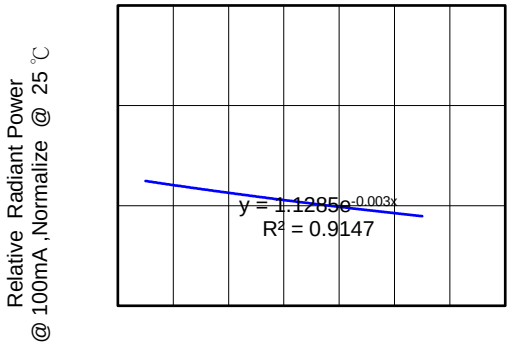


Fig 7. Wavelength vs. Temperature
(Forward DC current @100mA)

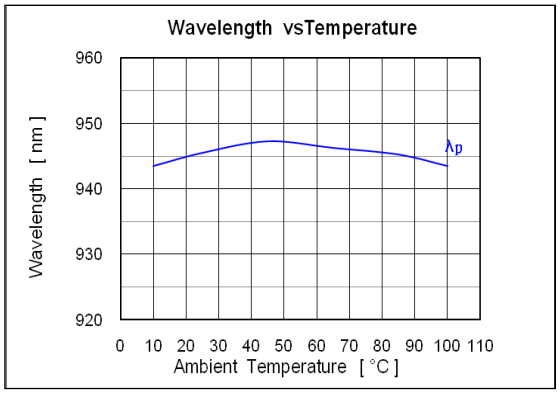



Fig 8.Maximum Driving Forward DC Current vs. Ambient Temperature (De-rating based on Tj max.=115℃)